

RF Power MOSFET Transistor 5 W, 2 - 175 MHz, 28 V

Rev. V1

Features

- N-Channel enhancement mode device
- DMOS structure
- Lower capacitances for broadband operation
- · High saturated output power
- · Lower noise figure than bipolar devices
- RoHS Compliant

ABSOLUTE MAXIMUM RATINGS AT 25° C

| Parameter | Symbol | Rating | Units |
|----------------------|------------------|-------------|-------|
| Drain-Source Voltage | V_{DS} | 65 | V |
| Gate-Source Voltage | V_{GS} | 20 | V |
| Drain-Source Current | I _{DS} | 1.4 | Α |
| Power Dissipation | P _D | 15.8 | W |
| Junction Temperature | TJ | 200 | °C |
| Storage Temperature | T _{STG} | -55 to +150 | °C |
| Thermal Resistance | θ _{JC} | 11.1 | °C/W |

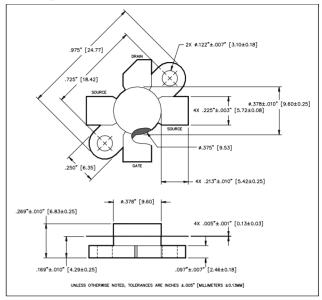
TYPICAL DEVICE IMPEDANCE

| F (MHz) | Z _{IN} (Ω) | Z _{LOAD} (Ω) | | |
|---|---------------------|-----------------------|--|--|
| 100 | 15 - j121.0 | 57.0 + j23.0 | | |
| 150 | 39.0 - j77.0 | 55.0 +j23.0 | | |
| 175 | 41.0 - j38.0 | 56.0 + j19.0 | | |
| 200 | 56.0 + j20.0 | | | |
| V_{DD} = 28V, I_{DQ} = 50mA, P_{OUT} = 5W | | | | |

 Z_{IN} is the series equivalent input impedance of the device from gate to source.

Z_{LOAD} is the optimum series equivalent load impedance as measured from drain to ground.

Package Outline



| LETTER | MILLIMETERS | | INCHES | |
|--------|-------------|-------|--------|------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 24.64 | 24.89 | .970 | .980 |
| В | 18.29 | 18.54 | .720 | .730 |
| С | 20.07 | 20.83 | .790 | .820 |
| D | 9.47 | 9.73 | .373 | .383 |
| E | 6.22 | 6.48 | .245 | .255 |
| F | 5.64 | 5.79 | .222 | .228 |
| G | 2.92 | 3.30 | .115 | .130 |
| Н | 2.29 | 2.67 | .090 | .105 |
| J | 4.04 | 4.55 | .159 | .179 |
| К | 6.58 | 7.39 | .259 | .291 |
| L | .10 | .15 | .004 | .006 |

FLECTRICAL CHARACTERISTICS AT 25°C

| Parameter | Symbol | Min | Max | Units | Test Conditions |
|--------------------------------|-------------------|-----|------|-------|--|
| Drain-Source Breakdown Voltage | BV _{DSS} | 65 | - | V | V _{GS} = 0.0 V , I _{DS} = 20.0 mA |
| Drain-Source Leakage Current | I _{DSS} | - | 1.0 | mA | V _{GS} = 28.0 V , V _{GS} = 0.0 V |
| Gate-Source Leakage Current | I _{GSS} | - | 1.0 | μA | V _{GS} = 20.0 V , V _{DS} = 0.0 V |
| Gate Threshold Voltage | $V_{GS(TH)}$ | 2.0 | 6.0 | V | V _{DS} = 10.0 V , I _{DS} = 10 mA |
| Forward Transconductance | G_{M} | 80 | - | S | V_{DS} = 10.0 V , I_{DS} = 10 mA , Δ V_{GS} = 1.0 V, 80 μ s Pulse |
| Input Capacitance | C _{ISS} | - | 7 | pF | V _{DS} = 28.0 V , F = 1.0 MHz |
| Output Capacitance | Coss | - | 5 | pF | V _{DS} = 28.0 V , F = 1.0 MHz |
| Reverse Capacitance | C _{RSS} | - | 2.4 | pF | V _{DS} = 28.0 V , F = 1.0 MHz |
| Power Gain | G _P | 11 | - | dB | V _{DD} = 28.0 V, I _{DQ} = 50 mA, P _{OUT} = 5.0 W F =175 MHz |
| Drain Efficiency | ŋ _D | 55 | - | % | V _{DD} = 28.0 V, I _{DQ} = 50 mA, P _{OUT} = 5.0 W F =175 MHz |
| Load Mismatch | VSWR-T | - | 20:1 | - | V_{DD} = 28.0 V, I_{DQ} = 50 mA, P_{OUT} = 5.0 W F =175 MHz |

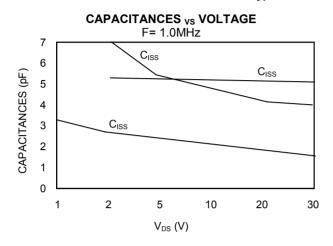
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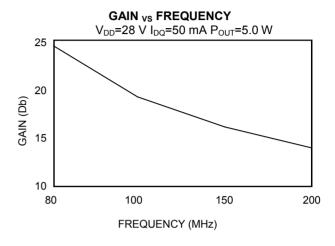


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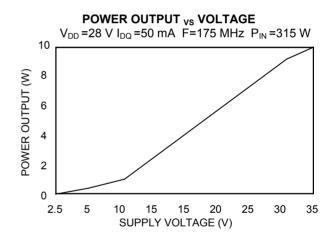
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Typical Broadband Performance Curves





POWER OUTPUT vs POWER INPUT $V_{DD} = 28 \text{ V } I_{DQ} = 50 \text{ mA}$ 6 175MHz POWER OUTPUT (W) 5 4 200MHz 150MHz 3 2 0.01 0.2 0.2 0.3 0.4 0.45 0.4 0.1 POWER INPUT (W)

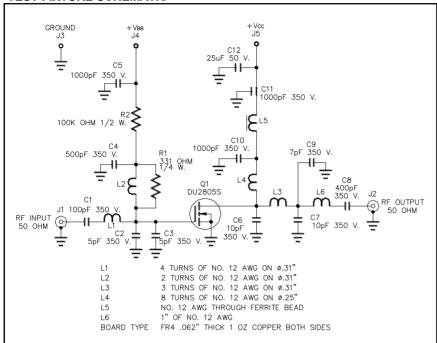




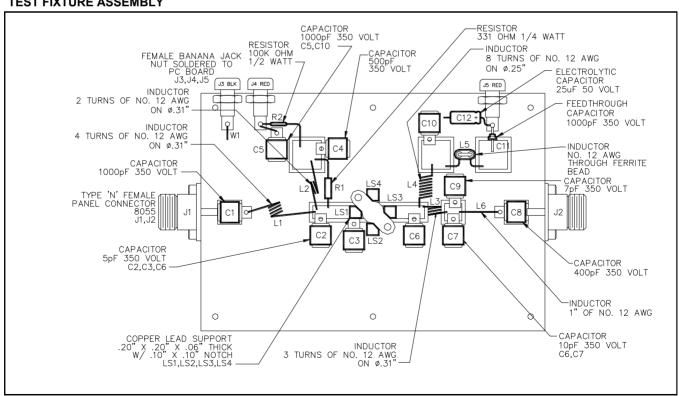
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TEST FIXTURE ASSEMBLY



DU2805S



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